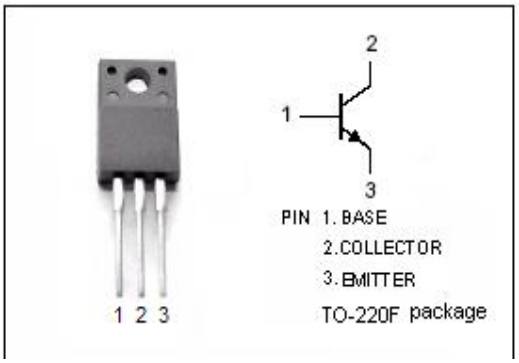
isc Silicon NPN Power Transistor — 2SD1499

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 100V (Min)
- Wide Area of Safe Operation
- Complement to Type 2SB1063
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

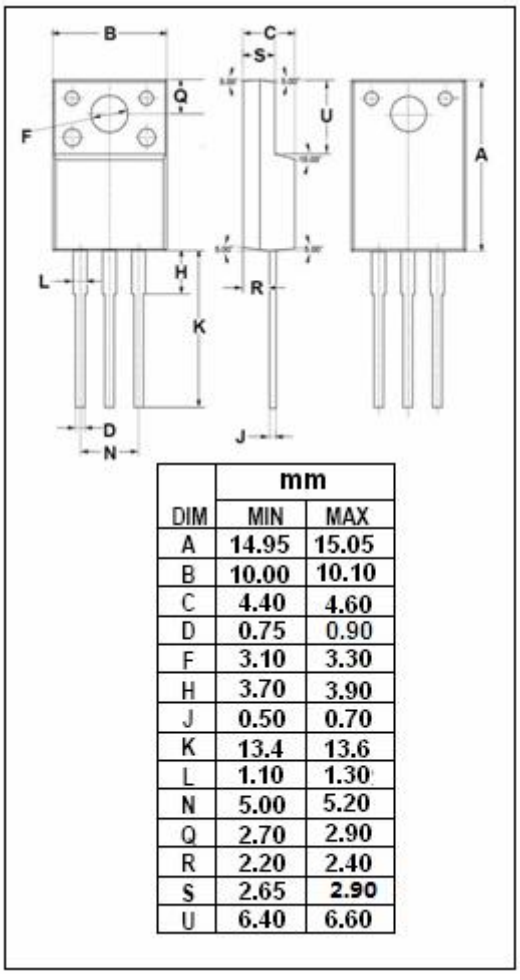


APPLICATIONS

- Designed for high power amplifications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	8	A
P_C	Collector Power Dissipation @ T_C=25℃	40	W
	Collector Power Dissipation @ T_a=25℃	2	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA ; I_B= 0	100			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 3A; I_B= 0.3A			2.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 3A ; V_{CE}= 5V			1.8	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 100V; I_E= 0			50	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 3V; I_C= 0			50	μA
h_{FE-1}	DC Current Gain	I_C= 20mA ; V_{CE}= 5V	20			
h_{FE-2}	DC Current Gain	I_C= 1A ; V_{CE}= 5V	60		200	
h_{FE-3}	DC Current Gain	I_C= 3A ; V_{CE}= 5V	20			
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 5V; f_{test}= 1.0MHz		20		MHz
C_{OB}	Output Capacitance	I_E=0 ; V_{CB}= 10V;f_{test}= 1.0MHz		90		pF

◆ **h_{FE-2} classifications**

Q	P
60-120	100-200

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